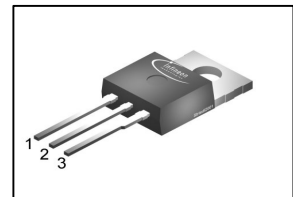


CoolMOS[®] Power Transistor
Features

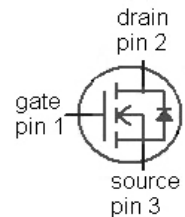
- New revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge
- Ultra low effective capacitances

Product Summary

| | | |
|--|------|----------|
| V_{DS} | 800 | V |
| $R_{DS(on)max}$ @ $T_j = 25^\circ\text{C}$ | 0.29 | Ω |
| $Q_{g,typ}$ | 88 | nC |

PG-TO220-3

CoolMOS[™] 800V designed for:

- Industrial application with high DC bulk voltage
- Switching Application (i.e. active clamp forward)



| Type | Package | Marking |
|------------|------------|---------|
| SPP17N80C3 | PG-TO220-3 | 17N80C3 |

Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|---|----------------|--|-------------|------------------|
| Continuous drain current | I_D | $T_C=25^\circ\text{C}$ | 17 | A |
| | | $T_C=100^\circ\text{C}$ | 11 | |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | $T_C=25^\circ\text{C}$ | 51 | |
| Avalanche energy, single pulse | E_{AS} | $I_D=3.4\text{ A}, V_{DD}=50\text{ V}$ | 670 | mJ |
| Avalanche energy, repetitive t_{AR} ^{2),3)} | E_{AR} | $I_D=17\text{ A}, V_{DD}=50\text{ V}$ | 0.5 | |
| Avalanche current, repetitive t_{AR} ^{2),3)} | I_{AR} | | 17 | A |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS}=0\dots640\text{ V}$ | 50 | V/ns |
| Gate source voltage | V_{GS} | static | ± 20 | V |
| | | AC ($f>1\text{ Hz}$) | ± 30 | |
| Power dissipation | P_{tot} | $T_C=25^\circ\text{C}$ | 227 | W |
| Operating and storage temperature | T_j, T_{stg} | | -55 ... 150 | $^\circ\text{C}$ |
| Mounting torque | | M3 and M3.5 screws | 60 | Ncm |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|-------------------------------------|---------------|--------------------|-------|------|
| Continuous diode forward current | I_S | $T_C=25\text{ °C}$ | 17 | A |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | | 51 | |
| Reverse diode dv/dt ⁴⁾ | dv/dt | | 4 | V/ns |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|---|------------|--------------------------------------|---|---|------|-----|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 0.55 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | leaded | - | - | 62 | |
| Soldering temperature, wave soldering only allowed at leads | T_{sold} | 1.6 mm (0.063 in.) from case for 10s | - | - | 260 | °C |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

| | | | | | | |
|----------------------------------|---------------|---|-----|------|------|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$ | 800 | - | - | V |
| Avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{ V}$, $I_D=17\text{ A}$ | - | 870 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_D=1.0\text{ mA}$ | 2.1 | 3 | 3.9 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ | - | - | 25 | μA |
| | | $V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$ | - | 150 | - | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}$, $I_D=11\text{ A}$, $T_j=25\text{ °C}$ | - | 0.25 | 0.29 | Ω |
| | | $V_{GS}=10\text{ V}$, $I_D=11\text{ A}$, $T_j=150\text{ °C}$ | - | 0.67 | - | |
| Gate resistance | R_G | $f=1\text{ MHz}$, open drain | - | 0.85 | - | Ω |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|--|--------------|---|---|------|---|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ | - | 2300 | - | pF |
| Output capacitance | C_{oss} | $f=1\text{ MHz}$ | - | 94 | - | |
| Effective output capacitance, energy related ⁵⁾ | $C_{o(er)}$ | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V | - | 72 | - | |
| Effective output capacitance, time related ⁶⁾ | $C_{o(tr)}$ | | - | 210 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=17\text{ A},$ $R_G=4.7\ \Omega, T_j=25\text{ }^\circ\text{C}$ | - | 25 | - | ns |
| Rise time | t_r | | - | 15 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 72 | - | |
| Fall time | t_f | | - | 12 | - | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|---------------|---|---|-----|-----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=640\text{ V}, I_D=17\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 12 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 45 | - | |
| Gate charge total | Q_g | | - | 88 | 117 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.5 | - | V |

Reverse Diode

| | | | | | | |
|-------------------------------|-----------|---|---|-----|-----|---------------|
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=I_S=17\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 1 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=400\text{ V},$ $I_F=I_S=17\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 550 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 15 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 51 | - | A |

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

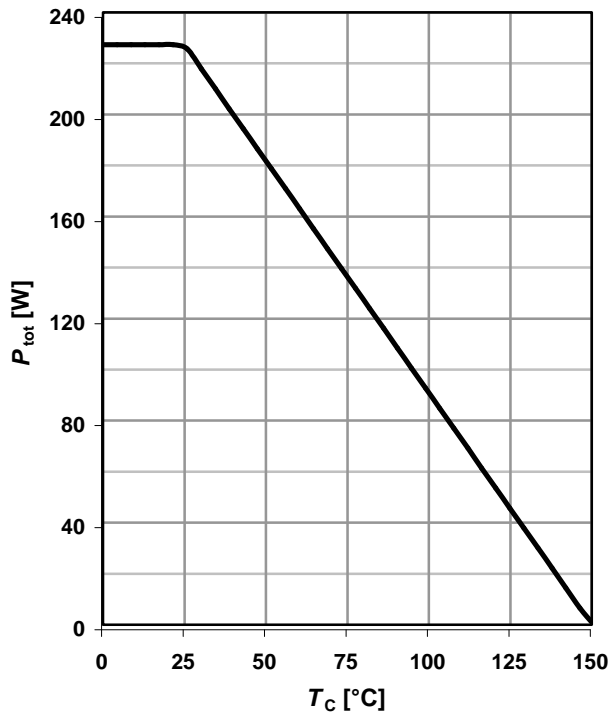
⁴⁾ $I_{SD}=I_D, di/dt=200\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak}<V_{(BR)DSS}, T_j<T_{j,max}$, identical low side and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

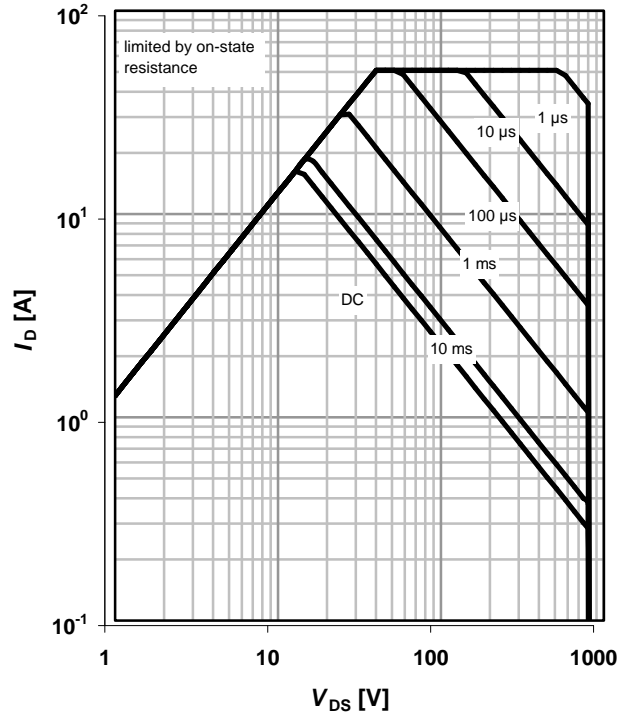
$$P_{tot}=f(T_C)$$



2 Safe operating area

$$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$$

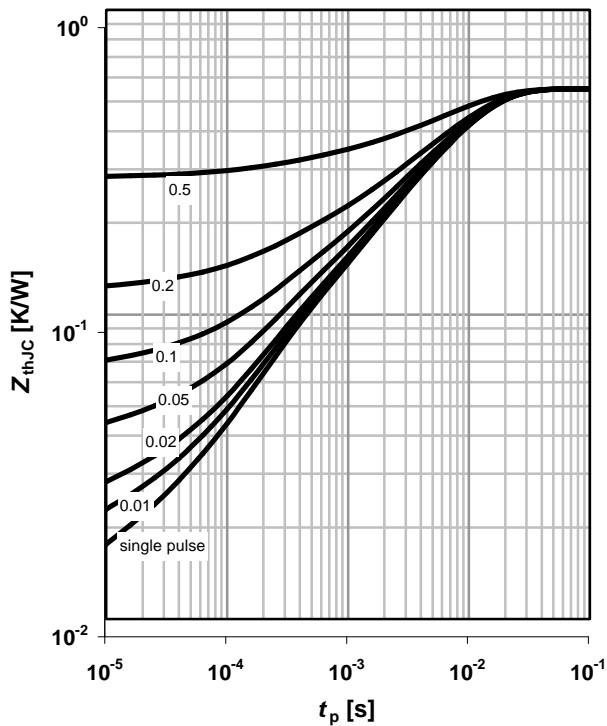
parameter: t_p



3 Max. transient thermal impedance

$$Z_{thJC}=f(t_p)$$

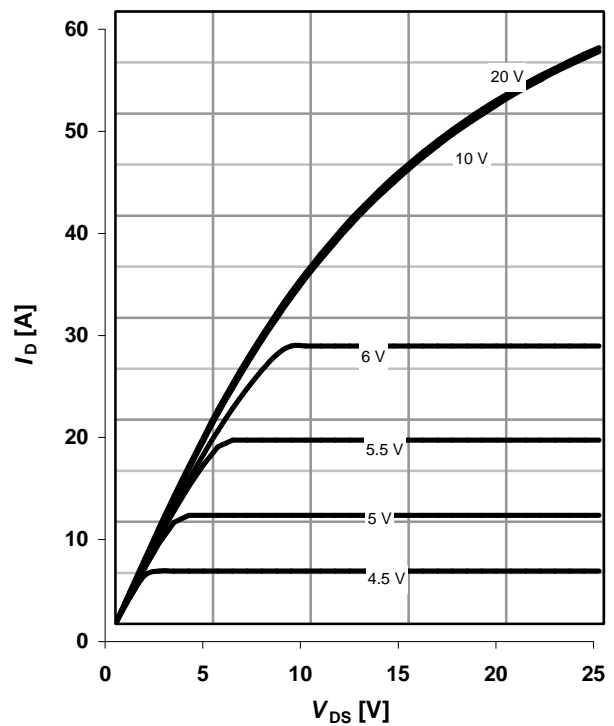
parameter: $D=t_p/T$



4 Typ. output characteristics

$$I_D=f(V_{DS}); T_j=25\text{ °C}; t_p=10\text{ μs}$$

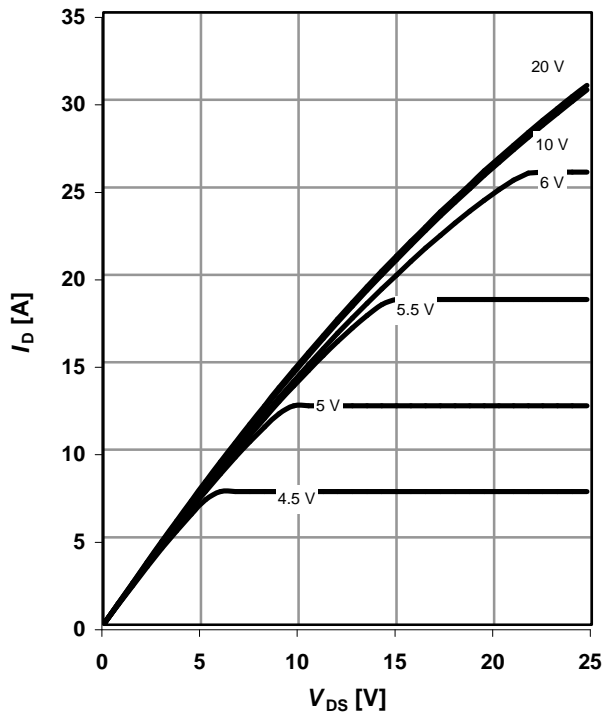
parameter: V_{GS}



5 Typ. output characteristics

$I_D=f(V_{DS}); T_j=150\text{ }^\circ\text{C}; t_p=10\text{ }\mu\text{s}$

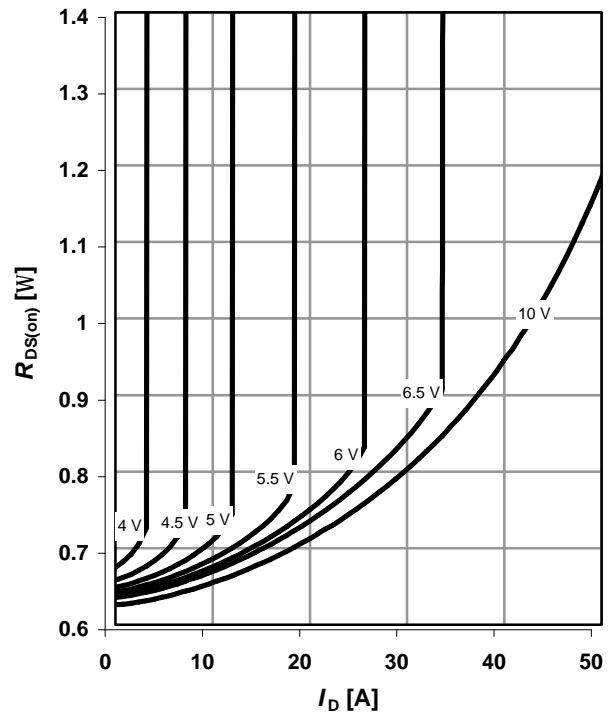
parameter: V_{GS}



6 Typ. drain-source on-state resistance

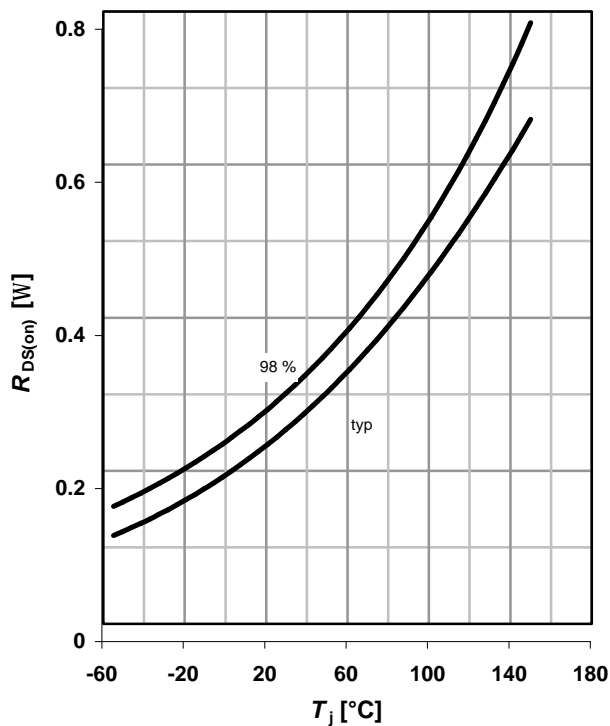
$R_{DS(on)}=f(I_D); T_j=150\text{ }^\circ\text{C}$

parameter: V_{GS}



7 Drain-source on-state resistance

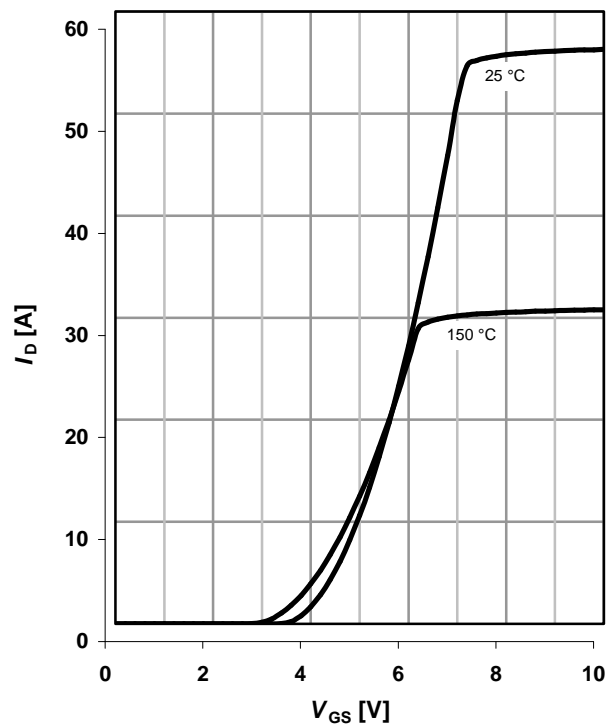
$R_{DS(on)}=f(T_j); I_D=11\text{ A}; V_{GS}=10\text{ V}$



8 Typ. transfer characteristics

$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}; t_p=10\text{ }\mu\text{s}$

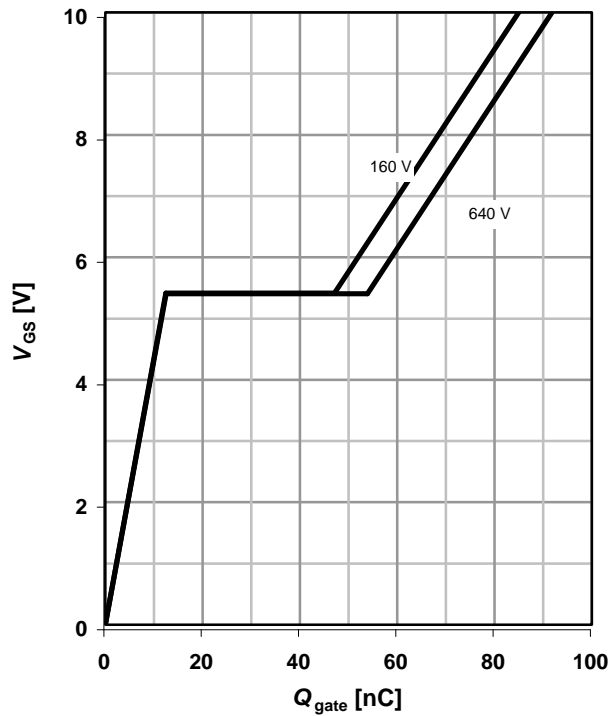
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=17\text{ A pulsed}$

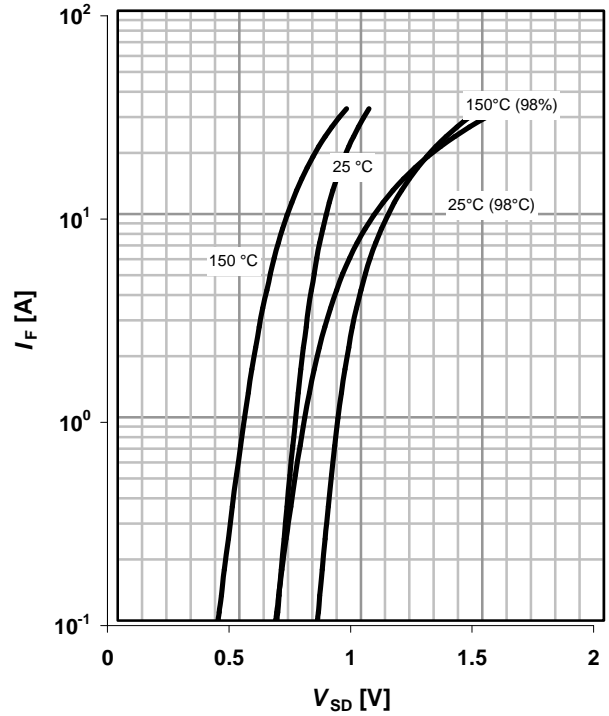
parameter: V_{DD}



10 Forward characteristics of reverse diode

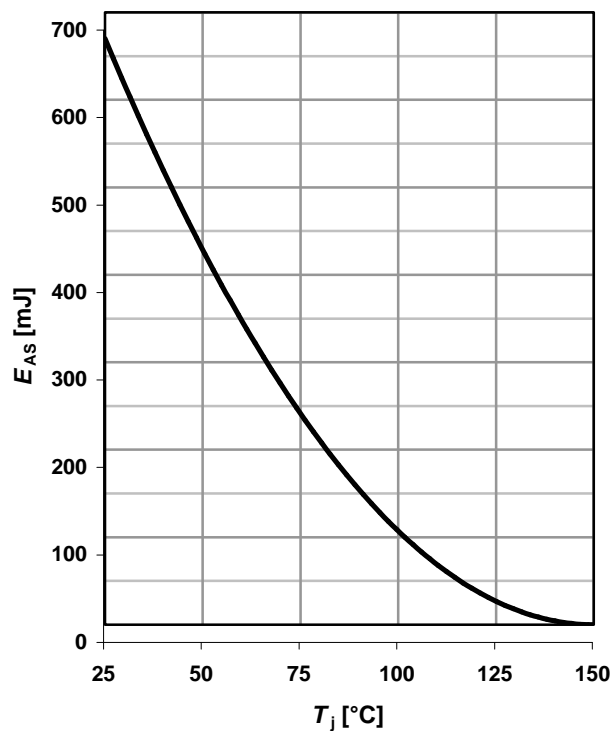
$I_F=f(V_{SD}); t_p=10\ \mu\text{s}$

parameter: T_j



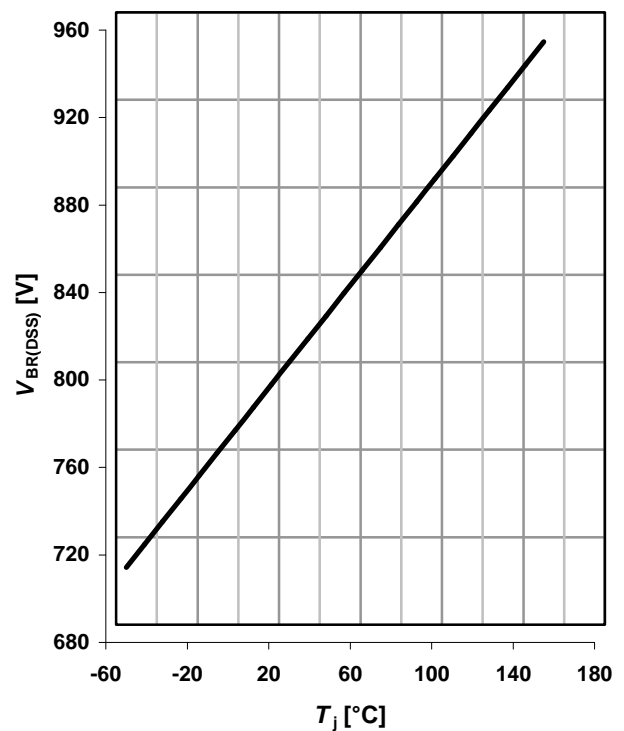
11 Avalanche energy

$E_{AS}=f(T_j); I_D=3.4\text{ A}; V_{DD}=50\text{ V}$



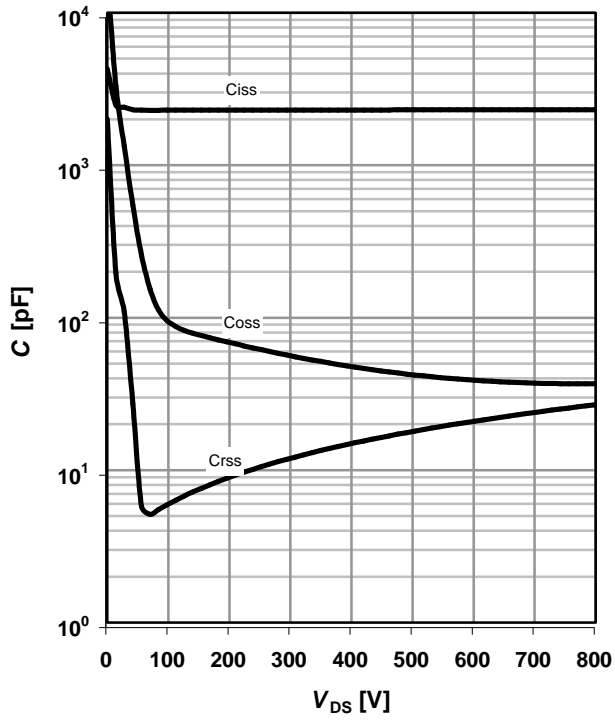
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



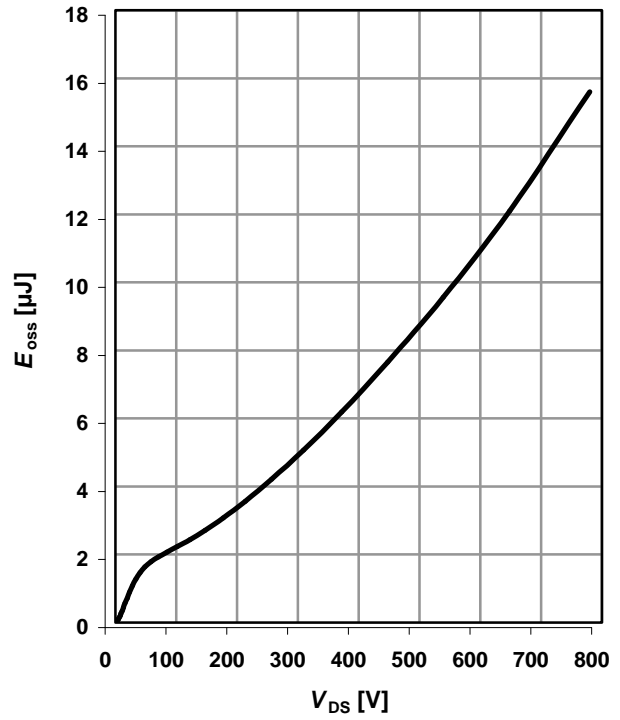
13 Typ. capacitances

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

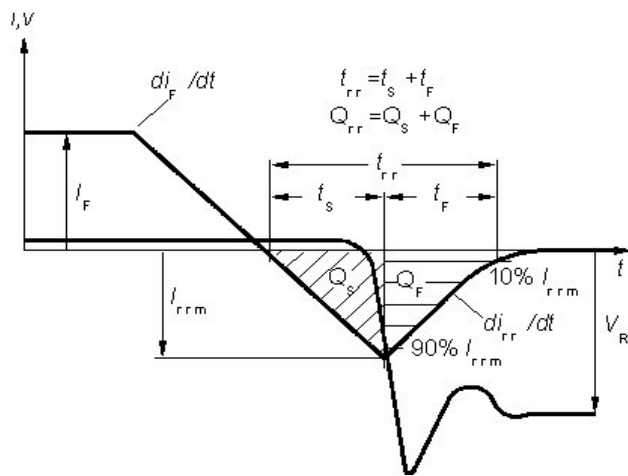


14 Typ. Coss stored energy

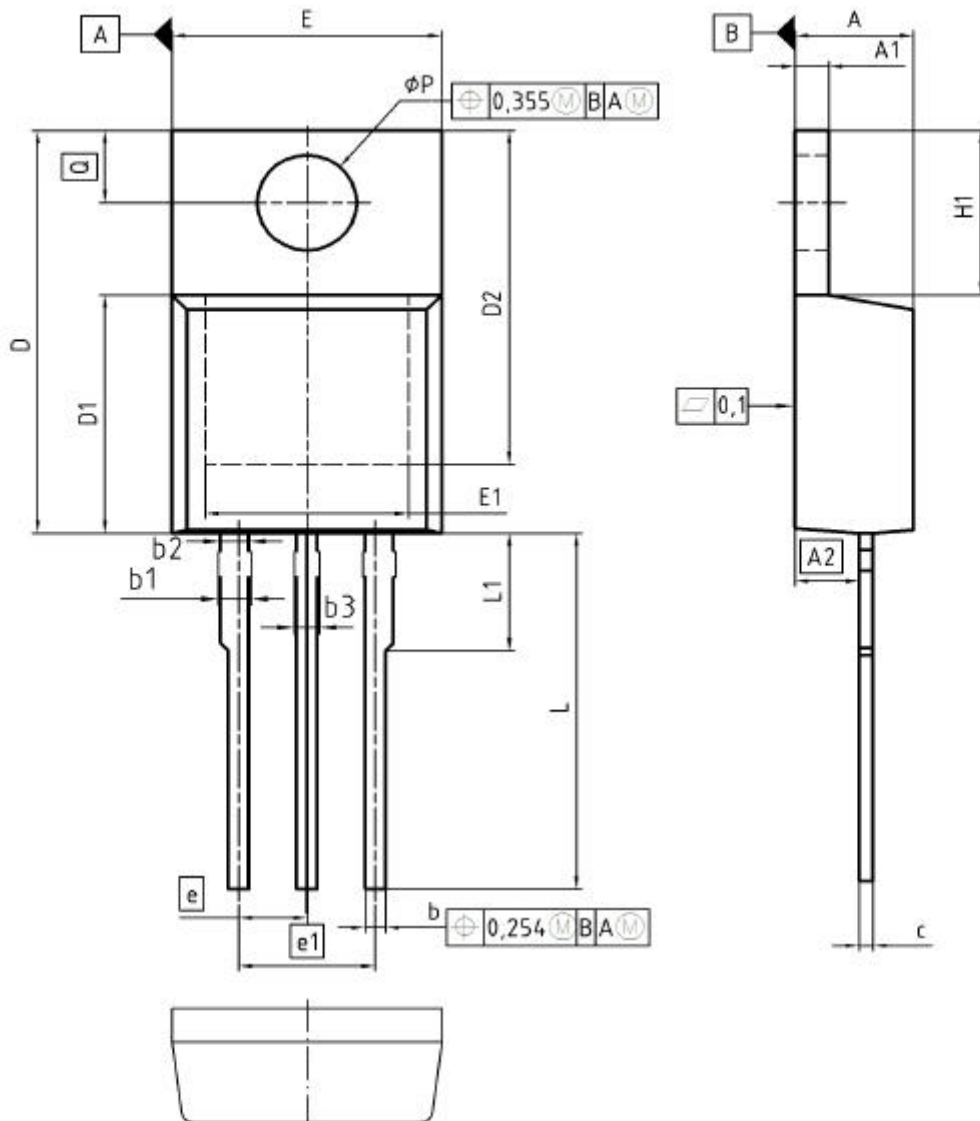
$E_{oss}=f(V_{DS})$



Definition of diode switching characteristics



PG-TO220-3: Outline



| DIM | MILLIMETERS | | INCHES | |
|----------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| ϕP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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